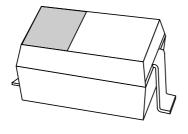
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2015EALow V_F (MEGA) Schottky barrier diode

Product specification

2003 May 20





Low V_F (MEGA) Schottky barrier diode

PMEG2015EA

FEATURES

Forward current: 1.5 AReverse voltage: 20 V

• Ultra high-speed switching

• Very low forward voltage

• Very small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- · Voltage clamping
- · Protection circuits.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode

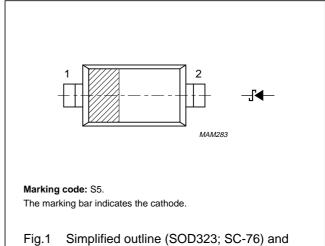


Fig.1 Simplified outline (SOD323; SC-76) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	20	V
I _F	continuous forward current	T _s < 55 °C	_	1.5	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave	_	10	Α
I _{FRM}	repetitive peak forward current	$t_p = 1 \text{ ms}; \ \delta = \le 0.25$	_	4.5	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2; note 1			
		I _F = 10 mA	240	270	mV
		I _F = 100 mA	300	350	mV
		I _F = 1000 mA	480	550	mV
		I _F = 1500 mA	560	660	mV
I _R	continuous reverse current	see Fig.3; note 1			
		V _R = 5 V	5	10	μΑ
		V _R = 8 V	7	20	μΑ
		V _R = 15 V	10	50	μΑ
C _d	diode capacitance	V _R = 5 V; f = 1 MHz; see Fig.4	19	25	pF

Note

1. Pulse test: $t_p = 300 \ \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	450	K/W
	ambient	note 2	210	K/W
R _{th j-s}	thermal resistance from junction to solder point	note 3	90	K/W

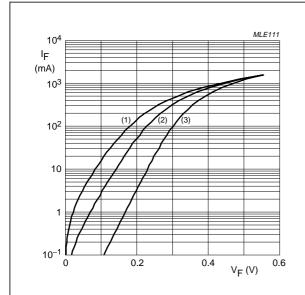
Notes

- 1. Refer to SC-76 (SOD323) standard mounting conditions.
- 2. Device mounted on a printed-circuit board with copper clad 10 x 10 mm.
- 3. Soldering point of cathode tab.

Low V_F (MEGA) Schottky barrier diode

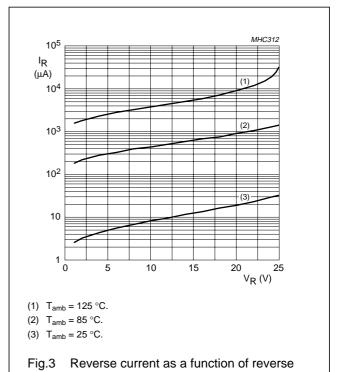
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GRAPHICAL DATA

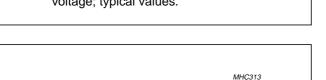


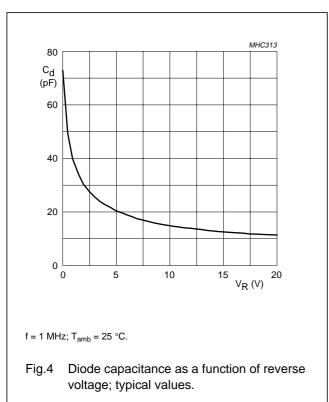
- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



voltage; typical values.





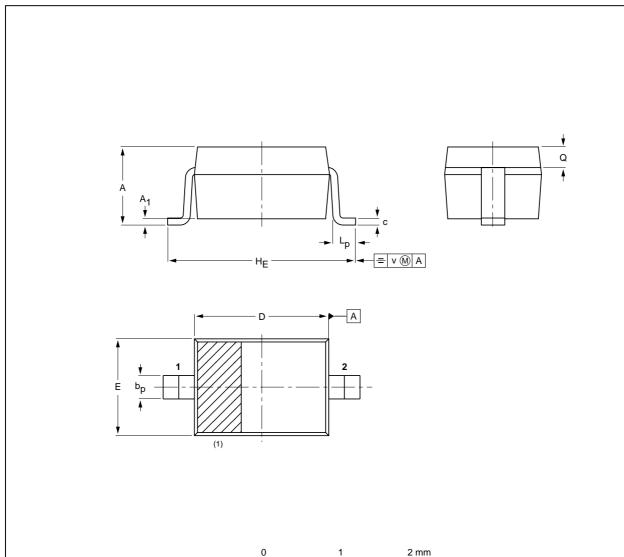
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	bp	С	D	Е	HE	Lp	Q	v
mm		+ 0.05 - 0.05				1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	VERSION IEC JEDEC		EIAJ			PROJECTION
SOD323			SC-76			98-09-14 99-09-13

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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